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- (71) Applicant: **APPLIED MATERIALS, INC.** [US/US];
3050 Bowers Avenue, Santa Clara, California 95054 (US).
- (72) Inventors: **ERICKSON, Blake**; 3050 Bowers Avenue,
Santa Clara, California 95054 (US). **BERDING, Keith**;
3050 Bowers Avenue, Santa Clara, California 95054 (US).
KUTNEY, Michael; 3050 Bowers Avenue, Santa Clara,
California 95054 (US). **BARMAN, Soumendra**; 3050

Bowers Avenue, Santa Clara, California 95054 (US). **ZHU, Zhaozhao**; 3050 Bowers Avenue, Santa Clara, California 95054 (US). **SANPEDRO, Michelle**; 3050 Bowers Avenue, Santa Clara, California 95054 (US). **RAO, Suresh Polali Narayana**; 3050 Bowers Avenue, Santa Clara, California 95054 (US).

- (74) Agent: **PORTNOVA, Marina** et al.; LOWENSTEIN SANDLER LLP, One Lowenstein Drive, Roseland, New Jersey 07068 (US).

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- (54) Title: MULTIPLE REFLECTOMETRY FOR MEASURING ETCH PARAMETERS

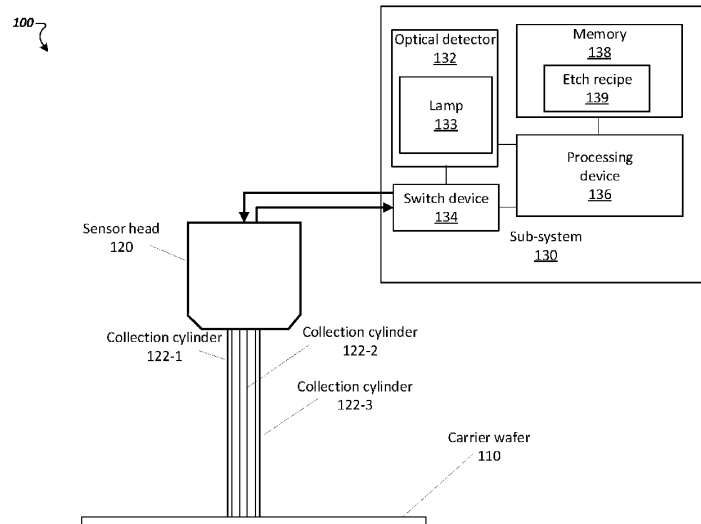


FIG. 1

- (57) Abstract: A system includes a memory and at least one processing device operatively coupled to the memory to facilitate an etch recipe development process by performing a number of operations. The operations include receiving a request to initiate an iteration of an etch process using an etch recipe to etch a plurality of materials each located at a respective one of a plurality of reflectometry measurement points, obtaining material thickness data for each of the plurality of materials resulting from the iteration of the etch process, and determining one or more etch parameters based on the material thickness data.

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